TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK3476

# VHF- and UHF-band Amplifier Applications

Unit: mm

• Output power: PO = 7.0 W (min)

• Gain: Gp = 11.4dB (min)

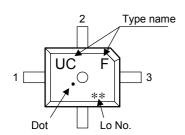
• Drain efficiency:  $\eta D = 60\%$  (min)

## **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DSS</sub>	20	V
Gain-source voltage	$V_{GSS}$	±5	٧
Drain current	I <sub>D</sub>	3	Α
Power dissipation	P <sub>D</sub> (Note 1)	20	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-45~150	°C

Note 1: Tc = 25°C (When mounted on a 1.6 mm glass epoxy PCB)

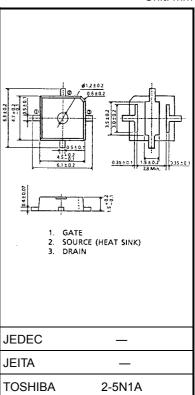
# Marking



- 1. Gate
- 2. Source (heat sink)
- 3. Drain

#### Caution

Please take care to avoid generating static electricity when handling this transistor.



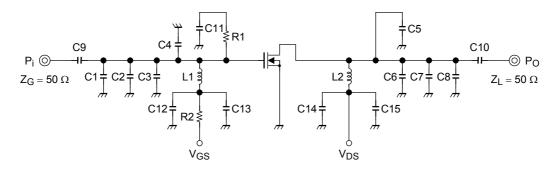
### **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	5	μА
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = 10 V	_	_	5	μА
Threshold voltage	V <sub>th</sub>	$V_{DS} = 7.2 \text{ V}, I_D = 2 \text{ mA}$	0.55	1.05	1.55	V
Drain-source on-voltage	V <sub>DS</sub> (ON)	$V_{GS} = 10 \text{ V}, I_D = 75 \text{ mA}$	_	18		mV
Forward transconductance	Y <sub>fs</sub>	V <sub>DS</sub> = 7.2 V, I <sub>DS</sub> = 1 A	_	1		S
Input capacitance	C <sub>iss</sub>	$V_{DS} = 7.2 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	53		pF
Output capacitance	Coss	$V_{DS} = 7.2 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	49	_	pF
Output power	Po	V <sub>DS</sub> = 7.2 V,	7	_	_	W
Drain efficiency	η <sub>D</sub>	I <sub>idle</sub> = 500 mA (V <sub>GS</sub> = adjust),	60	_	_	%
Power gain	G <sub>P</sub>	f = 520 MHz, P <sub>i</sub> = 500 mW,	11.4	_	_	dB
Low voltage output power	P <sub>OL</sub>	$\begin{split} &V_{DS}=6.0~\text{V},\\ &I_{idle}=500~\text{mA}~\text{(V}_{GS}=\text{adjust)},\\ &f=520~\text{MHz},~\text{P}_i=500~\text{mW}, \end{split}$	5	_	_	W
Load mismatch	_	$\begin{split} &V_{DS}=10 \text{ V, P}_O=7 \text{ W,} \\ &V_{GS}=\text{adjust, P}_i=\text{adjust,} \\ &f=520 \text{ MHz,} \\ &VSWR \text{ LOAD 20:1 all phase} \end{split}$	No degradation			

Note 1: These characteristic values are measured using measurement tools specified by Toshiba.

#### **Output Power Test Fixture**

(Test Condition: f = 520 MHz,  $V_{DS} = 7.2 \text{ V}$ ,  $I_{idle} = 500 \text{ mA}$ ,  $P_i = 500 \text{ mW}$ )



C1: 15 pF

L1:  $\phi$ 0.6 mm enamel wire, 5.8ID, 4T C2: 11 pF L2:  $\phi$ 0.6 mm enamel wire, 5.8ID, 8T R1:  $2.2 \Omega$ R2: 1.5 kΩ

C3: 9 pF

C4: 30 pF

C5: 30 pF

C6: 11 pF

C7: 8 pF

C8: 9 pF

C9: 2200 pF

C10: 2200 pF

C11: 2200 pF

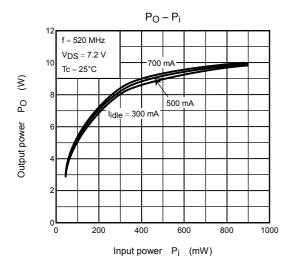
C12: 10000 pF

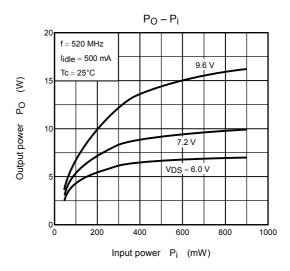
C13: 10 μF

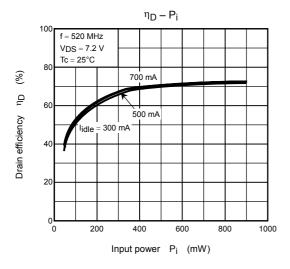
C14: 10000 pF

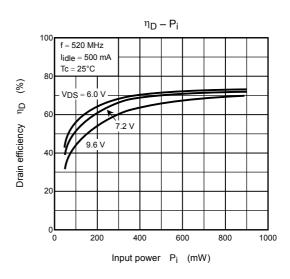
C15: 10 μF

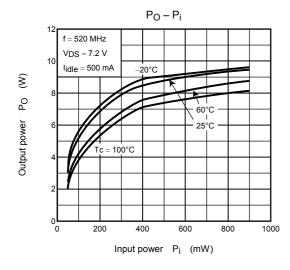
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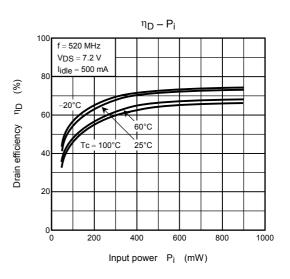












Note 2: These are only typical curves and devices are not necessarily guaranteed at these curves.

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